

FORM PTO-1449 (SUBSTITUTE) U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE STATEMENT BY APPLICANT (37 CFR 1.98(b))				Attorney Docket No.: CIP of Applic. No. GR 98 P 1801 09/232,081 <u>Ser No: 09/363277</u> Applicant Kai Wurster et al. Filing Date of CIP Group Art Unit July 28, 1999 2811-2812			
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EXAMINER INITIALS	PATENT NO.	DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE
<i>gm</i>	A	5,187,550	02/93	Yanagisawa		
<i>gm</i>	B	5,670,805	09/97	Hammerl et al.		
<i>gm</i>	C	4,937,205	06/90	Nakayama et al.		
<i>gm</i>	D	5,344,381	09/94	Cabrera y Lopez Caram		
<i>gm</i>	E	5,336,912	08/94	Ohtsuki		
<i>gm</i>	F	5,360,758	11/94	Bronner et al.		
<i>gm</i>	G	5,250,829	10/93	Bronner et al.		
	H					
	I					

FOREIGN PATENT DOCUMENT							
DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB CLASS	TRANSL. YES	TRANSL. NO	
<i>gm</i>	J	0 621 632 A1	10/94	Europe		X	
	K						
	L						
	M						
	N						

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)	
<i>gm</i>	"Shallow n ⁺ Junctions in Silicon by Arsenic Gas-Phase Doping" (Ransom et al.), Journal of the Electrochemical Society, Vol. 141, No. 5, pages 1378-1381;
<i>gm</i>	"Low Pressure Deposition of Doped SiO ₂ by Pyrolysis of Tetraethylorthosilicate (TEOS) (Becker), Journal of the Electrochemical Society, Vol. 136, No. 10, pages 3033-3043.

EXAMINER <i>Jennifer M. Kennedy</i>	DATE CONSIDERED <i>1/2/2002</i>
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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L							
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)	
	"0.228μm ² Trench Cell Technologies with Bottle-Shaped Capacitor for 1Gbit DRAMs" (Ozaki et al.), IEDM 95, pages 661-664.

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